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Complete set of claims

1(canceled).

2(canceled).

3(canceled).

4(canceled).

5(currently amended). A process for producing a semiconductor device, comprising the steps of: forming an insulating layer and an etching stopper layer on a substrate; removing part of the insulating layer by dry etching; and filling an electrically conductive material into a groove or hole thus formed, wherein said etching stopper layer is formed by curing a composition comprising a silicon-containing polymer, wherein 5% to 100% by mole, based on the total number of moles of silicon contained in the silicon-containing polymer, of silicon is contained in a disilylbenzene structure, further where the silicon-containing polymer has a carbon content of not less than 30% by weight, and further where the etching stopper layer is cured at a temperature in the range of 200°C to 500°C for 30 to 50 minutes.

6(canceled).

7(canceled).

8(canceled).

9(canceled).

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10(canceled).

11(canceled).

12(canceled).

13(canceled).

14(canceled).

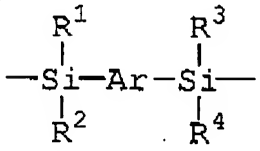
15(canceled).

16(canceled).

17(canceled).

18(canceled).

19(previously presented). The process of claim 5, where the disilylbenzene structure is represented by formula (I),



(I)

wherein R^1 to R^4 each independently are selected from hydrogen, an alkyl group, an alkenyl group, a cycloalkyl group, an aryl group, an aralkyl group, an alkylamino group, and an alkylsilyl group, and Ar represents an aryl group.

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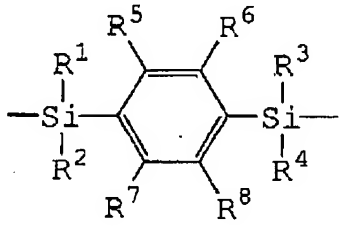
20(previously presented). The process of claim 5, where the disilylbenzene structure is represented by formula (II),



(II)

wherein R^1 to R^4 each independently are selected from hydrogen, an alkyl group, an alkenyl group, a cycloalkyl group, an aryl group, an aralkyl group, an alkylamino group, and an alkylsilyl group; and R^5 to R^8 are independently selected from hydrogen, a C_1 to C_3 alkyl group, a halogen atom, a C_1 to C_3 alkoxide group, and a C_1 to C_3 amino group.

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